Search Histon => d/18 1-17 abs,bib

(HEATHUS, INSPEC, SAPERO, CISPATAU)
3/14/25

ANSWER 1 OF 17 HCAPLUS COPYRIGHT 2005 ACS on STN L8

A photonic crystal manufacturing method exposes ≥2 Ag AΒ halide particle layers that contain Ag halide particles which have different spectral sensitivity characteristics for each of the Ag halide particle layers to light having wavelengths corresponding to the resp. different spectral sensitivity characteristics, and then develops the exposed Ag halide particle layers to form therein a periodic structure with an aggregate of developed Ag. Photonic crystals can be manufactured with relative ease in a relatively short period of time. This method assures continued high accuracy.

AN 2004:251809 HCAPLUS

DN 140:278343

Method of manufacturing photonic crystal TI

IN Miyazaki, Keiichi

PA Fuji Photo Film Co., Ltd., Japan

U.S. Pat. Appl. Publ., 7 pp. SO CODEN: USXXCO

DT Patent

English LΑ

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE	
ΡI	US 2004055528	A1	20040325	US 2003-667361	20030923	
	JP 2004117479	A2	20040415	JP 2002-276867	20020924	
PRAI	JP 2002-276867	Α.	20020924			

ANSWER 2 OF 17 HCAPLUS COPYRIGHT 2005 ACS on STN L<sub>8</sub>

A single-beam holog. method for one-step fabrication of three-dimensional (3D) metallodielec. photonic crystals is demonstrated using a 632.8 nm He-Ne laser. A top-cut triangular prism is used to split an incident plane wave into four beams and then to combine them to form a 3D interference pattern. A silver halide holog, plate is used to record the interference pattern and then a 3D structure with embedded Ag particles is created. A strongly damping band around 1400 nm is observed in the transmission spectrum of this 3p structure.

AN 2003:733735 HCAPLUS

DN

Holography for one-step fabrication of three-dimensional metallodielectric photonic crystals with a single continuous. TI wavelength laser beam

Wang, Guo Ping; Tan, Chunlei: Ai Nong Lang, Shan, Hong ΑU

Dep. of Phys., and Sch. of Computer Sci., Wuhan Univ., Wuhan, 430072, CS Peop. Rep. China

Journal of Modern Optics (2003), 50(14), 2155-2161 SO CODEN: JMOPEW; ISSN: 0950-0340

PB Taylor & Francis Ltd.

DТ Journal

English T.A

RE.CNT 20 THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT

L8 ANSWER 3 OF 17 INSPEC (C) 2005 IEE on STN

AN 2004:7903470 INSPEC. DN A2004-09-4240-015; B2004-04-4350-079

AB A single-beam holographic method for one-step fabrication of three-dimensional (3D) metallodielectric photonic crystals is demonstrated using a 632.8 nm He-Ne laser. A top-cut triangular prism is used to split an incident plane wave into four beams and then to combine them to form a 3D interference pattern. A silver halide holographic plate is used to record the interference pattern and then a 3D structure with embedded Ag particles is created. A strongly damping band around 1400 nm is observed in the

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A2004-09-4240-015; B2004-04-4350-079
DN
      Holography for one-step fabrication of three-dimensional metallodielectric
ΤI
      photonic crystals with a single continuous
      wavelength laser beam.
      Guo Ping Wang; Chunlei Tan; Yongxiang Yi; Hong Shan (Dept. of Phys., Wuhan
ΑU
      Univ., China)
      Journal of Modern Optics (20 Sept. 2003) vol.50, no.14, p.2155-61. 20
SO
      refs.
      Published by: Taylor & Francis
      CODEN: JMOPEW ISSN: 0950-0340
      SICI: 0950-0340(20030920)50:14L.2155:HSFT;1-#
DT
      Journal
      Experimental
TC
CY
      United Kingdom
      English
T.A
      ANSWER 4 OF 17 JAPIO (C) 2005 JPO on STN
T.R
      2004-117479
ΑN
                          JAPIO
      PROBLEM TO BE SOLVED: To provide a manufacturing method for
AR
      photonic crystal in which the photonic
      crystal can be manufactured relatively easily in a relatively
      short time and further a manufacturing method for photonic crystal which can maintain high precision.

SOLUTION: The present invention is characterized in that two or more silver halide layers containing silver halide particles with mutually different spectral sensitivity characteristics are exposed to lights having wavelengths corresponding to the different spectral sensitivity characteristics and developed to form periodic statutures of aggregates of developed silver
      developed to form periodic structures of aggregates of developed silver in
      the silver halide particle layer COPYRIGHT: (C) 2004 DE0 2004-117479
AN
      METHOD FOR MANUFACTURING PHOTONIC CRYSTAL
TI
      MIYAZAKI KEIICHI
IN
      FUJI PHOTO FILM CO LTD
PA
PΙ
      JP 2004117479 A 20040415 Heisei
      JP 2002-276867 (JP2002276867 Heisei) 20020924
AΙ
PRAI JP 2002-276867
                                20020924
      PATENT ABSTRACTS OF JAPAN (CD-ROM), Unexamined Applications, Vol. 2004
SO
      ANSWER 5 OF 17 USPATFULL ON STN
L8
AB
         A novel anisotropic spectral scattering film is disclosed. The scattered
         light intensity Fx(\lambda, \theta) at azimuthal angle \theta and
         incident wavelength \lambda in an arbitrary scattering plane
         with respect to a surface of the film, and the scattered light intensity
         Fy(\lambda,\theta) at azimuthal angle \theta and incident
         wavelength \lambda in a scattering plane orthogonal to said
         scattering plane satisfy the following equations (1) and (2):
         Fx(\lambda, \theta)/Fx(545, \theta) \ge 1.2
                                           (1)
         \{Fx(\lambda, \theta)/Fx(545, \theta)-Fy(\lambda, \theta)/Fy(545, \theta)\}
         θ)}≥0.1
                      (2)
         provided that \lambda is 435 or 610 nm and \theta is an arbitrary
         angle selected from 30-70°.
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
         2005:2856 USPATFULL
AN
         Anisotropic spectral scattering films polarizers and liquid crystal
TI
IN
         Amimori, Ichiro, Minami-ashiqara-shi, XAPAN
```

transmission spectrum of this 3D structure.

```
Fujiwara, Isao, Minami-ashigara-shi, JAPAN
       Fuji Photo Film Co., Ltd., Minami-ashigara-shi, JAPAN (non-U.S.
PA
       corporation)
                                  20050106
       US 2005001957
PΙ
                            Α1
                                  20040514 (10)
       US 2004-845264
                            A1
ΑI
                             20030516
PRAI
       JP 2003-138772
       JP 2003-138773
                             20030516
DT
       Utility
       APPLICATION
FS
       BURNS DOANE SWECKER & MATHIS L L P, POST OFFICE BOX 1404, ALEXANDRIA,
LREP
       VA, 22313-1404
       Number of Claims: 13
CLMN
ECL
       Exemplary Claim: 1
DRWN
       8 Drawing Page(s)
LN.CNT 1573
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
     ANSWER 6 OF 17 USPATFULL oh STN
T.A
       Wafer-level electronic packages having waveguides and methods of
AB
        fabricating chip-level electronic packages having waveguides are
       disclosed. A representative chip-level electronic package includes at
       least one waveguide having a waveguide core. In addition, another representative chip-level electronic package includes a waveguide having an air-gap cladding layer around a portion of the waveguide core. A representative method for fabricating a chip-level electronic package
        includes: providing a substrate having a passivation layer disposed on
       the substrate; disposing a waveguide core on a portion of the
       passivation layer; disposing a first sacrificial layer onto at least one
       portion of the passivation layer and the waveguide core; disposing an
       overcoat layer onto the passivation layer and the first sacrificial
       layer; and removing the first sacrificial layer to define an air-gap
        cladding layer within the overcoat polymer layer and around a portion of
        the wavequide core.
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN
        2004:333764 USPATFULL
       Guided-wave optical interconnections embedded within a microelectronic
TI
        wafer-level batch package
       Mule, Tony, Atlanta, GA, UNITED STATES
ΙN
        Patel, Chirag, Jonesboro, GA, UNITED STATES
       Meindl, James D., Marietta, GA, UNITED STATES
       Gaylord, Thomas K., Atlanta, GA, UNITED STATES
       Glytsis, Elias N., Dunwoody, GA, UNITED STATES
       Martin, Kevin P., Atlanta, GA, UNITED STATES
        Schultz, Stephen M., Spanish Fork, UT, UNITED STATES
        Bakir, Muhannad, Atlanta, GA, UNITED STATES
        Reed, Hollie, Smyrna, GA, UNITED STATES
        Kohl, Paul, Atlanta, GA, UNITED STATES
ΡI
                                  20041230
        US 2004264840
                            A1
       US 2004-895685
                                  20040721 (10)
ΑI
                            A1
        Continuation of Ser. No. US 2002, 74420, filed on 11 Feb 2002, GRANTED,
RLI
        Pat. No. US 6785458
PRAI
       US 2001-268142P
                              20010211 (60)
DT
       Utility
FS
       APPLICATION
       THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE
LREP
        1750, ATLANTA, GA, 30339-5948
       Number of Claims: 11
CLMN
        Exemplary Claim: CLM-01-30
ECL
DRWN
        40 Drawing Page(s)
LN.CNT 1528
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
```

```
ANSWER 7 OF 17 USPATFULL on STN
L8
        Continous, conducting metal patterns can be formed from metal
AB
        nanoparticle containing fils by exposure to radiation. The metal
        patterns can be one, two, or three dimensional and have high resolution
        resulting in feature sizes in the order of micron to nanometers
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
        2004:104811 USPATFULL
        Method for patterning metal using nanopraticle containing percursors
ΤI
        Perry, Joseph W., Tucson, AZ, UNITED STATES
IN
        Marder, Seth R., Tucson, AZ, UNITED STATES
        Stellacci, Francesco, Tucson, AZ, UNITED STATES
                           A1
                                    20040429
PΤ
        US 2004079195
        US 2003-450661
                              A1
                                    200$1215 (10)
ΑI
        WO 2001-US47724
                                    20011217
DT
        Utility
FS
        APPLICATION
        OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C., 1940 DUKE STREET,
LREP
        ALEXANDRIA, VA, 22314
        Number of Claims: 73
CLMN
ECL
        Exemplary Claim: 1
DRWN
        24 Drawing Page(s)
LN.CNT 2486
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
      ANSWER 8 OF 17 USPATFULL on $TN
        A feedback-enhanced light emitting device is disclosed. A feedback
AB
        element coupled to an emissi\gammae element allows the emissive element to
        emit collimated light by stimulated emission. Feedback elements that
        provide this function may include but are not limited to holographic
        reflectors with refractive index that varies at least in part
        periodically and continuously!
ΑN
        2004:92555 USPATFULL
        Feedback enhanced light emitting device
ΤI
        Magno, John N., Middletown, NJ, UNITED STATES
IN
        Koch, Gene C., Bayville, NJ, UNITED STATES
        Zeolux Corporation, Sammamish, WA, UNITED STATES (U.S. corporation)
PΑ
                             A1
                                    20040415
PΙ
        US 2004069995
                                    20030508 (10)
        US 2003-434941
                              A1
ΑI
                               20020508 (60)
PRAI
        US 2002-379141P
DT
        Utility
FS
        APPLICATION
        BAKER & MCKENZIE, 805 THIRD AVENUE, NEW YORK, NY, 10022
LREP
CLMN
        Number of Claims: 127
ECL
        Exemplary Claim: 1
DRWN
        11 Drawing Page(s)
LN.CNT 1748
      ANSWER 9 OF 17 USPATFULL on STN
L8
        A photonic crystal manufacturing method exposes we
AΒ
        or more silver halide particle layers that contain silver halide particles which have different spectral
        sensitivity characteristics for each of the silver
halide particle layers to light having wavelengths
corresponding to the respective hifterent spectral sensitivity
characteristics, and then develops the exposed silver
halide particle layers to form therein a periodic structure with
an aggregate of developed silver. Photonic crystals
        can be manufactured with relative ease in a relatively short period of
        time. This method assures continued high accuracy.
```

```
2004:73766 USPATFULL
AN
       Method of manufacturing photonic crystal
TT
       Miyazaki, Keiichi, Kanagawa, JAPAN
IN
                                . (bon V.SV corporation)
20040125
PA
       FUJI PHOTO FILM CO., LTD.
       US 2004055528
                           A1
PΙ
       US 2003-667361
                                2003 23
ΑI
PRAI
       JP 2002-27686
       Utility
DТ
       APPLICATION
FS
                            √2100 PENNSYLVANIA AVENUE, N.W., SUITE 800,
       SUGHRUE MIONY PLLCX
LREP
       WASHINGTON, DC,/20037
       Number of Claims: 19
CLMN
ECL
       Exemplary Claim: 1
       2 Drawing Page(s)
DRWN
LN.CNT 359
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
     ANSWER 10 OF 17 USPATFULL on STN
1.8
       Optoelectronic probe cards, methods of fabrication, and methods of use,
AB
       are disclosed. Briefly described, one exemplary embodiment includes an
       optoelectronic probe card adapted to test an electrical quality and an
       optical quality of an optoelectronic structure under test having
       electrical and optical components.
       2004:23382 USPATFULL
AN
       High input/output density optoelectronic probe card for wafer-level test of electrical and optical interconnect components, methods of
TI
       fabrication, and methods of use
       Mule, Tony, Atlanta, GA, UNITED STATES
IN
       Thacker, Hiren, Decatur, GA) UNITED STATES
       Bakir, Muhannad, Atlanta, GA, UNITED STATES
       Meindl, James D., Marietta, GA, UNITED STATES
       Gaylord, Thomas K., Atlanta, GA, UNITED STATES
       Martin, Kevin P., Atlanta, GA, UNITED STATES
       Kohn, Paul, Atlanta, GA, UNITED STATES
                                20040129
PΤ
       US 2004017215
                           A1
                                200303/17 (10)
       US 2003-390873
ΑI
                           A1
                            20020319 ($0)
       US 2002-365443P
PRAI
DT
       Utility
       APPLICATION
FS
       THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE
LREP
       1750, ATLANTA, GA, 30339-5948
CLMN
       Number of Claims: 54
ECL
       Exemplary Claim: 1
DRWN
       4 Drawing Page(s)
LN.CNT 1017
     ANSWER 11 OF 17 USPATFULL on STN
L8
       A light control material is provided for displaying color images having
AB
       microstructures either on its surface or within the material which
       reflect a selected color and bandwidth of light in accordance with their
       physical characteristics. In an exemplary embodiment, the
       microstructures are stepped structures which reflect a particular color
       and bandwidth of light in accordance with the height of the steps of the
       stepped structures. In alternative embodiment, the microstructures are
       ribbed structures or crystal like structures designed to reflect a
       selected color and bandwidth of light. In addition, methods of
       fabricating the material are provided.
       2003:329968 USPATFULL
AN
       Light control material for displaying color information, and images
TI
IN
       Steenblik, Richard A., Alpharetta, GA, UNITED STATES
       Hurt, Mark J., Duluth, GA, UNITED STATES
```

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Knotts, Michael E., Roswell, GA, UNITED STATES
       Nanoventions, Inc., Roswell, GA (U.S. corporation)
PÀ
                                20031218
ΡĪ
       US 2003232179
                          A1
       US 2003-351286
                           A1
                                20030123 (10)
ΑI
                            20020124 (60)
PRAI
       US 2002-352000P
                            20020124 (60)
       US 2002-351853P
       Utility
DT
       APPLICATION
FS
       Todd Deveau, Thomas, Kayden, Horstemeyer & Risley, LLP, Suite 1750, 100
LREP
       Galleria Parkway, Atlanta, GA, 30339
CLMN
       Number of Claims: 32
       Exemplary Claim: 1
ECL
       22 Drawing Page(s)
DRWN
LN.CNT 1512
     ANSWER 12 OF 17 USPATFULL on STN
L8
       The optical functional element contains aggregates of developed silver
AB
       grains obtained by developing silver halide grains
       arranged so as to constitute a periodical structure. The element
       includes a substrate and a medium layer The aggregates of the developed
       silver grains are arranged in the medium layer so as to constitute said
       periodical structure. The element is produced by first selectively
       exposing a photo-curing resin layer formed on said substrate in which
       the silver halide grains are dispersed so as to
       selectively photo-cure the photo-curing resin layer, then overall
       exposing the photo-curing resin layer to expose the silver
       halide grains in the photo-curing resin layer, and thereafter
       developing the photo-curing resin layer.
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
       2003:265124 USPATFULL
AN
       Optical functional element and method of producing the same
TI
       Nagao, Kimitoshi, Kanagawa, JAPAN
IN
       FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)
PA
                          A1
                                20031002
       US 2003186139
PΙ
       US 6767676
                           B2
                                20040727
                                20030326 (10)
       US 2003-396504
                           A1
ΑI
                            20020326
PRAI
       JP 2002-85851
                            20020807
       JP 2002-229702
       Utility
DT
FS
       APPLICATION
       SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., WASHINGTON, DC,
LREP
       Number of Claims: 15
CLMN
       Exemplary Claim: 1
ECL
DRWN
       3 Drawing Page(s)
LN.CNT 590
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
     ANSWER 13 OF 17 USPATFULL on STN
L8
       A system for imposing a filter between a vehicle driver's eyes and a
AB
       source of light including at least one detector facing inward into a
       compartment in the vehicle toward a likely position of the head of the
       vehicle driver and arranged to obtain images of the eyes of the driver
       and a processor coupled to the detector(s) and arranged to determine the
       location of the driver's eyes based on analysis of the images obtained
       by the detector(s) and to obtain information about objects exterior of
       the vehicle providing sources of light from the images obtained by the
       detector(s) based on reflections off of the driver's eyes, i.e., the
       position of such objects. A filter, such as a pixelated screen, is
       imposed between the sources of light and the driver's eyes based on the location of the driver's eyes and the information about the exterior
       objects providing the sources of light.
```

```
2003:242806 USPATFULL
AN
       Enhanced vision for driving
ΤI
       Spero, Yechezkal Evan, Moshav Tifrach, ISRAEL
IN
PΙ
       US 2003169213
                          A1
                                20030911
       US 2003-383997
                                20030307 (10)
ΑI
                           Α1
PRAI
       US 2002-362078P
                            20020307 (60)
                            2002/0604 (60)
       US 2002-384845P
       Utility
DT
       APPLICATION
FS
       BRIAN ROFFE, ESQ, 11 SUNRISE PLAZA, SUITE 303, VALLEY STREAM, NY,
LREP
       11580-6170
CLMN
       Number of Claims: 20
       Exemplary Claim: 1
ECL
DRWN
       5 Drawing Page(s)
LN.CNT 1543
     ANSWER 14 OF 17 USPATFULL on STN
T.R
       Systems including apparatus, methods, compositions, and kits for
AB
       multiplexed analysis of biological samples or reagents using coded
       particles. The coded particles may be used to form positionally flexible
       arrays of samples and/or reagents in which the samples and/or reagents
       are identified by code's on the particles.
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN
       2003:187864 USPATFULL
       Coded particles for multiplexed analysis of biological samples
ΤI
       Ravkin, Ilya, Palo Alto, CA, UNITED STATES
IN
       Goldbard, Simon, San Jose, CA, UNITED STATES
       Zarowitz, Michael A., San Carlos, CA, UNITED STATES
       Hyun, William C., San Francisco, CA, UNITED STATES
PΙ
       US 2003129654
                          A1
                                20030710
ΑI
       US 2002-273605
                          A1
                                20021018 (10)
       Continuation-in-part of Ser. No. US 2000-549970, filed on 14 Apr 2000,
RLI
       PENDING Continuation-in-part of Ser. No. US 2000-694077, filed on 19 Oct
       2000, PENDING Continuation-in-part of Ser. No. US 2002-120900, filed on
       10 Apr 2002, PENDING
       WO 2001-US51413
PRAI
                            20011018
       US 2001-343682P
                            20011026 (60)
       US 2001-343685P
                            20011026
                                     (60)
       US 2001-344482P
                            20011026
                                     (60)
       US 2002-413675P
                            20020924
                                     (60)
                            20020221
                                     Ø60)
       US 2002-359207P
       US 2001-345606P
                            20011026 (60)
       US 2001-344483P
                            20011026 (60)
       US 1999-170947P
                            19991215 (60)
                            19990415 (60)
       US 1999-129664P
       US 2001-348025P
                            20011026 (6d)
                            20011026 (60)
       US 2001-348027P
       US 2002-362001P
                            20020305 (60)
       US 2002-362055P
                            20020305 (60)
       US 2002-362238P
                            20020305 (60)
       US 2002-370313P
                            20020404 (60)
       US 2002-383091P
                            20020523 (60)
       US 2002-383092P
                            20020523 (60)
       US 2002-413407P
                            20020924 (60)
DT
       Utility
FS
       APPLICATION
       KOLISCH HARTWELL, P.C., 520 S.W. YAMHILL STREET, SUITE 200, PORTLAND,
LREP
       OR, 97204
       Number of Claims: 65
CLMN
ECL
       Exemplary Claim: 1
DRWN
       22 Drawing Page(s)
```

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

ANSWER 15 OF 17 USPATFULL\on STN L8Wafer-level electronic packages having waveguides and methods of AB fabricating chip-level electronic packages having waveguides are disclosed. A representative chip-level electronic package includes at least one waveguide having a waveguide core. In addition, another representative chip-level electronic package includes a waveguide having an air-gap cladding layer around a portion of the waveguide core. A representative method for fabricating a chip-level electronic package includes: providing a substrate having a passivation layer disposed on the substrate; disposing a waveguide core on a portion of the passivation layer; disposing a first sacrificial layer onto at least one portion of the passivation layer and the waveguide core; disposing an overcoat layer onto the passivation layer and the first sacrificial layer; and removing the first sacrificial layer to define an air-gap cladding layer within the overcoat polymer layer and around a portion of the waveguide core. CAS INDEXING IS AVAILABLE FOR THIS PATENT. 2002:250548 USPATFULL AN Guided-wave optical interconnections embedded within a microelectronic ΤI wafer-level batch package Mule', Tony, Atlanta, GA, UNITED STATES IN Patel, Chirag, Jonesboro, GA, UNITED STATES Meindl, James D., Marietta, GA, UNITED STATES Gaylord, Thomas K., Atlanta, dA, UNITED STATES Glytsis, Elias N., Dunwoody, GA, UNITED STATES Martin, Kevin P., Atlanta, GA, UNITED STATES Schultz, Stephen M., Spanish Fdrk, UT, UNITED STATES Bakir, Muhannad, Atlanta, GA, UNITED STATES Reed, Hollie, Smyrna, GA, UNITED STATES Kohl, Paul, Atlanta, GA, UNITED STATES PΙ US 2002136481 A1 20020926 US 6785458 B2 20040831 20020211 1(10) US 2002-74420 A1 ΑI 20010211 (60) US 2001-268142P PRAI DT Utility FS APPLICATION THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE LREP 1750, ATLANTA, GA, 30339-5948 Number of Claims: 30 CLMN Exemplary Claim: 1 ECL DRWN 34 Drawing Page(s) LN.CNT 1591 CAS INDEXING IS AVAILABLE FOR THIS PATENT. ANSWER 16 OF 17 USPAT2 on STN \ L8The optical functional element contains aggregates of developed silver AΒ grains obtained by developing silver halide grains arranged so as to constitute a periodical structure. The element includes a substrate and a medium layer. The aggregates of the developed silver grains are arranged in the medium layer so as to constitute said periodical structure. The element is produced by first selectively exposing a photo-curing resin layer formed on said substrate in which the silver halide grains are dispersed so as to selectively photo-cure the photo-chring resin layer, then overall exposing the photo-curing resin layer to expose the silver halide grains in the photo-curing resin layer, and thereafter developing the photo-curing resin layer.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

```
2003:265124 USPAT2
ΑN
       Optical functional element and method of producing the same
ΤI
       Nagao, Kimitoshi, Kanagawa, JAPAN
Fuji Photo Film Co., Ltd., Kanagawa, JAPAN (non-U.S. corporation)
IN
PA
                                  20040727
       US 6767676
                            B2
PΤ
       US 2003-396504
                                  2003\(\beta\)326 (10)
AΙ
PRAI
       JP 2002-85851
                              20020326
                              20020807
       JP 2002-229702
       Utility
DT
       GRANTED
FS
       Primary Examiner: McPherson, John A.; Assistant Examiner: Walke, Amanda
EXNAM
LREP
       Sughrue Mion, PLLC
CLMN
       Number of Claims: 15
       Exemplary Claim: 1
ECL
       10 Drawing Figure(s); 3 Drawing Page(s)
DRWN
LN.CNT 583
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
     ANSWER 17 OF 17 USPAT2 on STN
L8
       Wafer-level electronic packages having waveguides and methods of
AB
        fabricating chip-level electronic packages having waveguides are
        disclosed. A representative chip-level electronic package includes at
        least one waveguide having a waveguide core. In addition, another
       representative chip-level electronic package includes a waveguide having an air-gap cladding layer around a portion of the waveguide core. A
       representative method for fabricating a chip-level electronic package
        includes: providing a substrate having a passivation layer disposed on
        the substrate; disposing a waveguide core on a portion of the
       passivation layer; disposing a first sacrificial layer onto at least one
        portion of the passivation layer and the waveguide core; disposing an
        overcoat layer onto the passivation layer and the first sacrificial
        layer; and removing the first sacrificial layer to define an air-gap
        cladding layer within the overcoat polymer layer and around a portion of
        the waveguide core.
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
        2002:250548 USPAT2
AN
        Guided-wave optical interconnections embedded within a microelectronic
ΤI
        wafer-level batch package
        Mule', Tony, Atlanta, GA, United States
Patel, Chirag, College Park, GA, United States
IN
       Meindl, James D., Marietta, GA, United States
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        Georgia Tech Research Corporation, Atlanta, GA, United States (U.S.
PA
        corporation)
                                   20040831
PΙ
        US 6785458
        US 2002-74420
                                   20020211 \((10)
AΙ
        US 2001-268142P
                              20010211 (60)
PRAI
DT
        Utility '
        GRANTED
FS
       Primary Examiner: Glick, Edward J. Assistant Examiner: Artman, Thomas R
EXNAM
        Thomas, Kayden, Horstemeyer & Risley, LLP
LREP
        Number of Claims: 13
CLMN
ECL
        Exemplary Claim: 12
        210 Drawing Figure(s); 40 Drawing Page(s)
DRWN
LN.CNT 1538
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
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## (FILE 'HOME' ENTERED AT 10:16:25 ON 14 MAR 2005)

FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 10:16:47 ON 14 MAR 2005 L113360 S (PHOTONIC) (8A) (CRYSTAL#) L281171 S (SILVER(W) HALIDE) L322170 S (SPECTRAL(4A)SENSITIV?) L47468 S (CHEMICAL(4A)SENSITIZAT?) L5 1 S L1 AND L2 AND L3 AND L4 L6 28 S L1 AND L2 L7 782039 S (WAVELENGTH#) 17 S L6 AND L7 L8

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(FILE 'HOME' ENTERED AT 10:16:25 ON 14 MAR 2005) FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 10:16:47 ON 14 MAR 2005 L113360 S (PHOTONIC) (8A) (CRYSTAL#) 81171 S (SILVER(W) HALIDE) L2 22170 S (SPECTRAL (4A) SENSITIV?) L3 7468 S (CHEMICAL (4A) SENSITIZAT?) L4=> s 11 and 12 and 13 and 14 1 L1 AND L2 AND L3 AND L4 L5 => d abs,bib L5 ANSWER 1 OF 1 USPATFULL on STN AB A photonic crystal manufacturing method exposes two or more silver halide particle layers that contain silver halide particles which have different spectral sensitivity characteristics for each of the silver halide particle layers to light having wavelengths corresponding to the respective different spectral sensitivity characteristics, and then develops the exposed silver halide particle layers to form therein a periodic structure with an aggregate of developed silver. Photonic crystals can be manufactured with relative ease in a relatively short period of time. This method assures continued high accuracy. CAS INDEXING IS AVAILABLE FOR THIS PATENT. 2004:73766 USPATFULL AN TIMethod of manufacturing photonic crystal IN Miyazaki, Keiichi, Kanagawa, JAPAN FUJI PHOTO FILM CO., LTD. (non-U.S. corporation) PA 20040325 PΙ US 2004055528 A1 20030923 (10) ΑI US 2003-667361 A1 JP 2002-276867 20020924 PRAI DT Utility APPLICATION FS SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., SUITE 800, LREP WASHINGTON, DC, 20037 CLMN Number of Claims: 9 ECLExemplary Claim: 1 DRWN 2 Drawing Page(s) LN.CNT 359

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CAS INDEXING IS AVAILABLE FOR THIS PATENT.



## PALM INTRANET

Day : Monday Date: 3/14/2005

Time: 09:11:30

## **Inventor Name Search Result**

Your Search was:

Last Name = MIYAZAKI First Name = KEIICHI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
07278130	Not Issued	161	11/30/1988	PHOTOGRAPHIC PRINTS AND A METHOD FOR THEIR MANUFACTURE	MIYAZAKI, KEIICHI
08668588	5966701	150	06/19/1996	RECOGNITION AND JUDGEMENT APPARATUS HAVING VARIOUS LEARNING FUNCTIONS	MIYAZAKI, KEIICHI
09325546	6636631	150	06/04/1999	OPTICAL CHARACTER READING METHOD AND SYSTEM FOR A DOCUMENT WITH RULED LINES AND ITS APPLICATION	MIYAZAKI, KEIICHI
09478437	6500607	150	01/06/2000	SILVER HALIDE PHOTOGRAPHIC MATERIAL	MIYAZAKI, KEIICHI
<u>09604435</u>	6643407	150			MIYAZAKI, KEIICHI
<u>09819203</u>	Not Issued	094	03/28/2001	APPARATUS AND METHOD FOR REPRODUCING PICTURE SIGNAL	MIYAZAKI, KEIICHI
<u>09819955</u>	Not Issued	030	03/28/2001	APPARATUS AND METHOD FOR DECOMPRESSING COMPRESSED DATA	MIYAZAKI, KEIICHI
09820325	6842485	150	03/29/2001	METHOD AND APPARATUS FOR REPRODUCING COMPRESSIVELY CODED DATA	MIYAZAKI, KEIICHI
10254773	6773122	150		OPTICAL FILM CONTAINING ANTI-GLARE LAYER AND IMAGE DISPLAY APPARATUS USING THE SAME	MIYAZAKI, KEIICHI
<u>10667361</u>	Not Issued	030		METHOD OF MANUFACTURING	MIYAZAKI, KEIICHI

h e eb cg b e f

				PHOTONIC CRYSTAL	
10880471	Not Issued	030	07/01/2004	LIQUID CRYSTAL DISPLAY	MIYAZAKI, KEIICHI
10942144	Not Issued	020	09/16/2004	IMAGING DISPLAY APPARATUS	MIYAZAKI, KEIICHI
07425235	4981269	150	10/23/1989	VERTICAL MILL	MIYAZAKI, KEIICHIRO

Inventor Search Completed: No Records to Display.

Saarah Amathan	Last Name	First Name	
Search Another: I	Miyazaki	Keiichi	Search

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6, 467, 676

114 (89, 95, 97

10/667 361

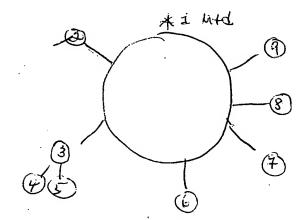
Inventor Nome Search Conspected

S(photonic) (82) (cmstal#)

S (silver (w) halide or S (spectral (4a) sensitiv?) Simuelengthat

schenical (go) sensitization#

10/117,479



Motivation - the production of a short crystal w/ since i a short